



STD35NF06

N-CHANNEL 60V - 0.018Ω - 35A DPAK

STripFET™II MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|-----------|------------------|---------------------|----------------|
| STD35NF06 | 60 V | < 0.024 Ω | 35 A |

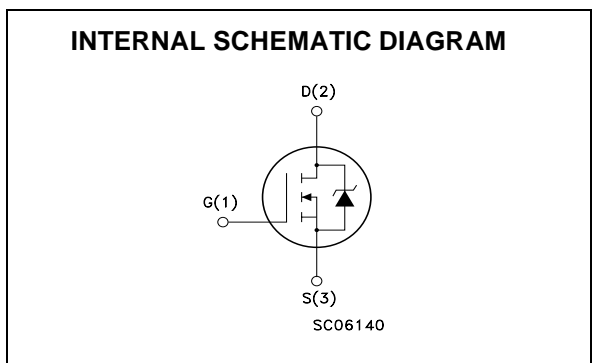
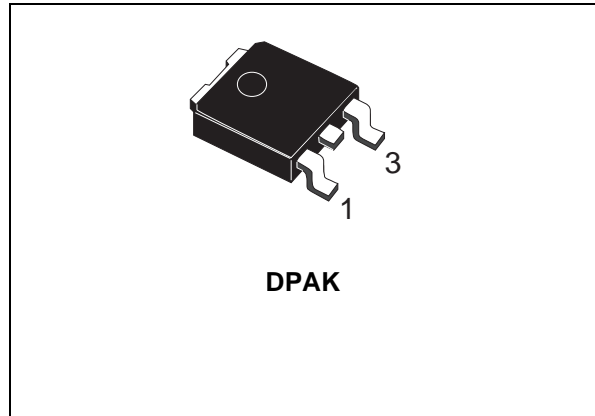
- TYPICAL R_{DS(on)} = 0.018 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED

DESCRIPTION

This Power Mosfet is the latest development of ST-Microelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 60 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 60 | V |
| V _{GS} | Gate- source Voltage | ± 20 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 35 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 24.5 | A |
| I _{DM} (●) | Drain Current (pulsed) | 140 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 55 | W |
| | Derating Factor | 0.37 | W/°C |
| dv/dt (1) | Peak Diode Recovery voltage slope | 5 | V/ns |
| T _{stg} | Storage Temperature | -55 to 175 | °C |
| T _j | Max. Operating Junction Temperature | | |

(*) Pulse width limited by safe operating area

(1) I_{SD} ≤ 35A, di/dt ≤ 100A/μs, V_{DD} ≤ V(BR)DSS, T_j ≤ T_{JMAX}.

STD35NF06

THERMAL DATA

| | | | |
|----------------|--|-----|------|
| Rthj-case | Thermal Resistance Junction-case Max | 2.7 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 100 | °C/W |
| T _I | Maximum Lead Temperature For Soldering Purpose | 275 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 17.5 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 130 | mJ |

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 60 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 10 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ± 20V | | | ±100 | nA |

ON (1)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|--|------|-------|-------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 17.5 A | | 0.018 | 0.024 | Ω |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (1) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 17.5 A | | 13 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 1530 | | pF |
| C _{OSS} | Output Capacitance | | | 300 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 105 | | pF |

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 30\text{ V}$, $I_D = 27.5\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3) | | 16 | | ns |
| t_r | Rise Time | | | 8 | | ns |
| Q_g | Total Gate Charge | $V_{DD} = 48\text{ V}$, $I_D = 55\text{ A}$, $V_{GS} = 10\text{ V}$ | | 44.5 | 60 | nC |
| Q_{gs} | Gate-Source Charge | | | 10.5 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 17.5 | | nC |

SWITCHING OFF

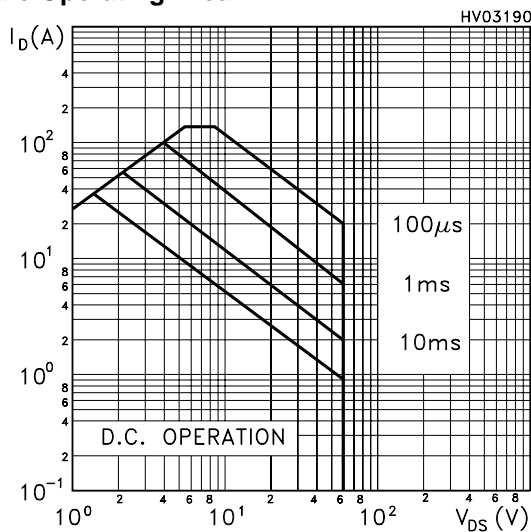
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|--|------|------|------|------|
| $t_{d(off)}$ | Turn-off-Delay Time | $V_{DD} = 30\text{ V}$, $I_D = 27.5\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3) | | 36 | | ns |
| t_f | Fall Time | | | 15 | | ns |

SOURCE DRAIN DIODE

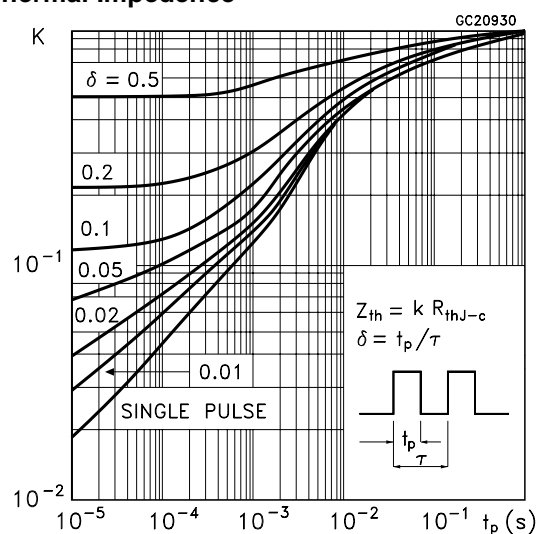
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--------------|-------------------------------|---|------|------|------|------|
| I_{SD} | Source-drain Current | | | | 35 | A |
| $I_{SDM(2)}$ | Source-drain Current (pulsed) | | | | 140 | A |
| $V_{SD(1)}$ | Forward On Voltage | $I_{SD} = 35\text{ A}$, $V_{GS} = 0$ | | | 1.5 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 35\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5) | | 75 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 170 | | nC |
| I_{RRM} | Reverse Recovery Current | | | 4.5 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

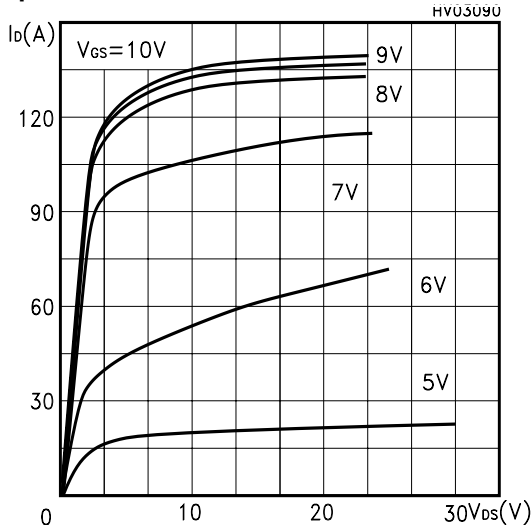
Safe Operating Area



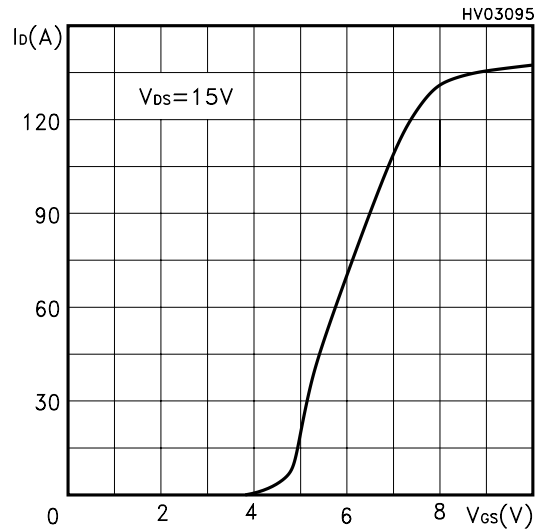
Thermal Impedance



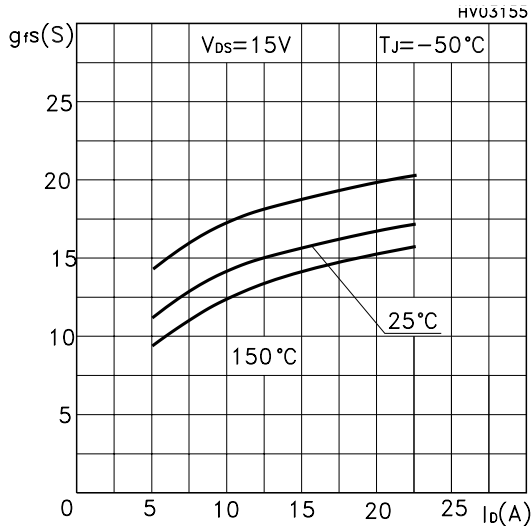
Output Characteristics



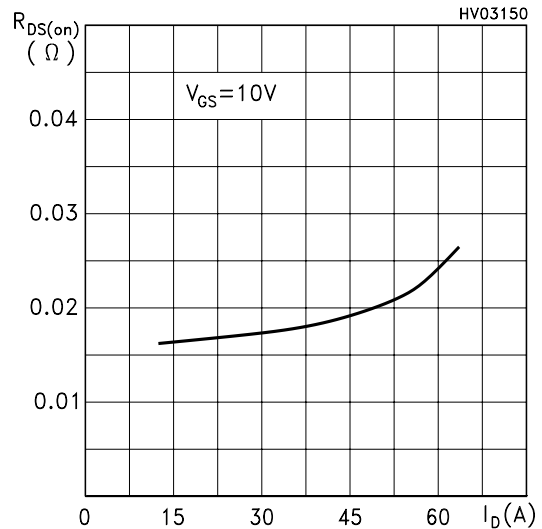
Transfer Characteristics



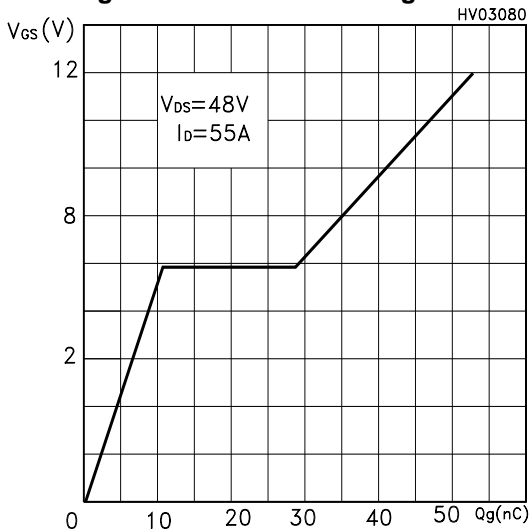
Transconductance



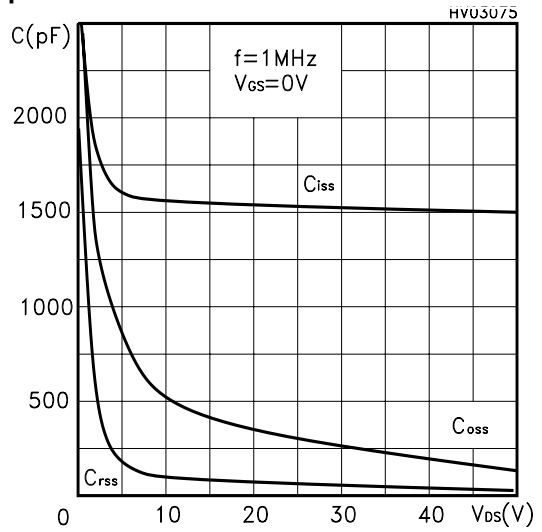
Static Drain-source On Resistance



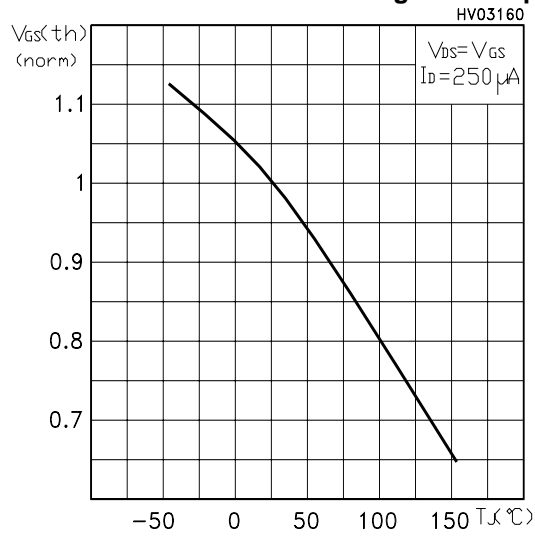
Gate Charge vs Gate-source Voltage



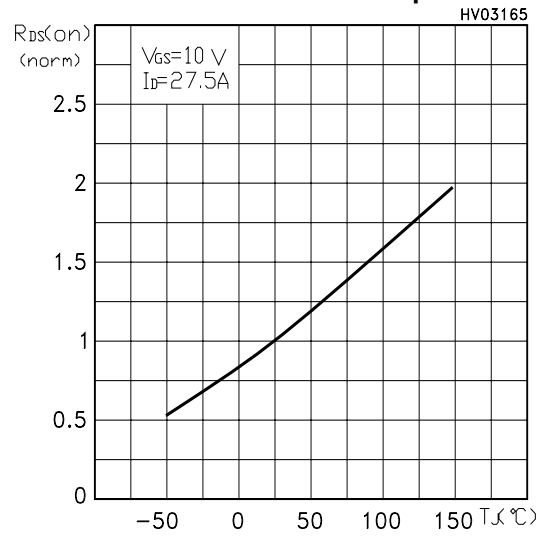
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

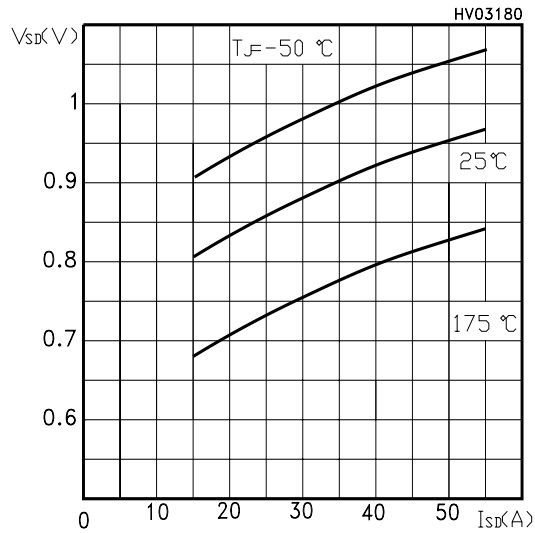


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuit For Resistive Load



Fig. 4: Gate Charge test Circuit

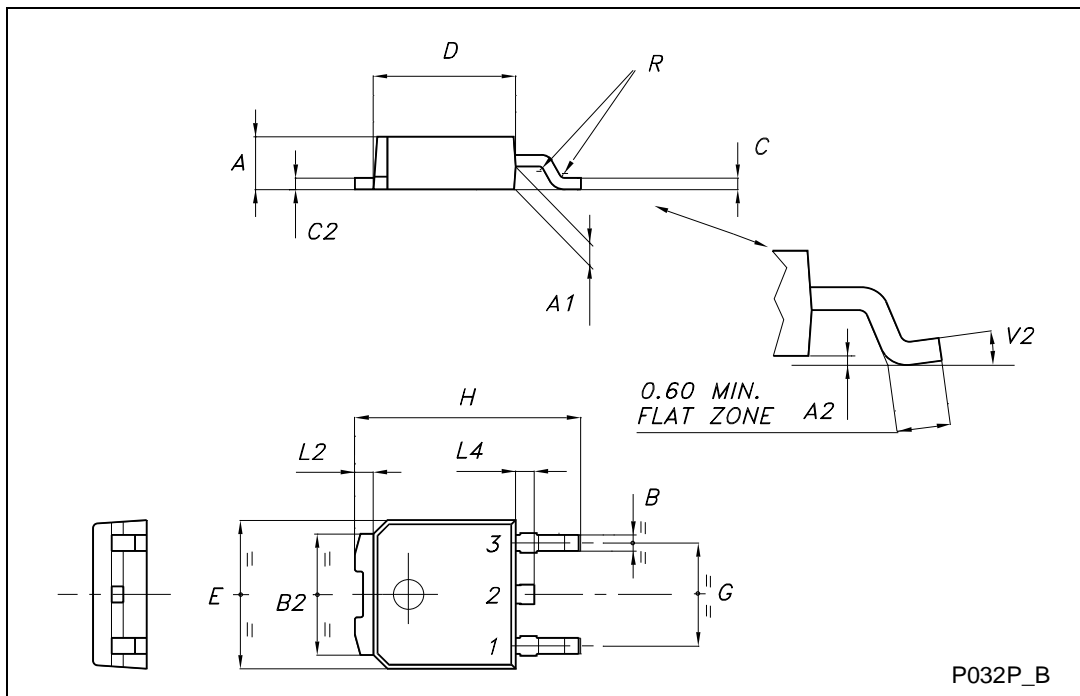


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

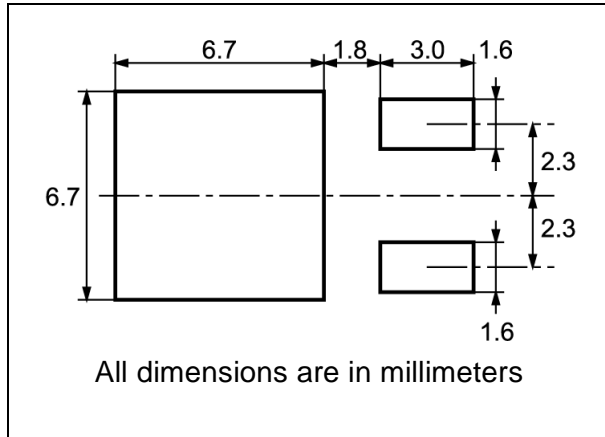


TO-252 (DPAK) MECHANICAL DATA

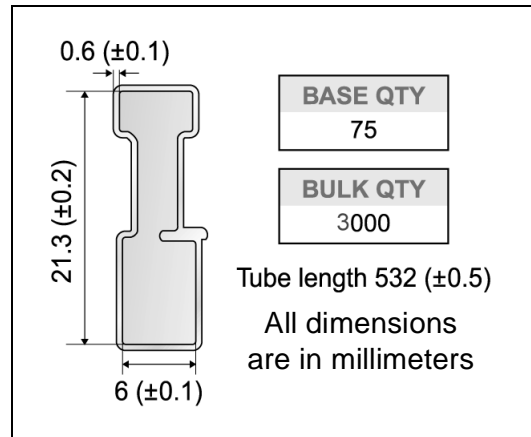
| DIM. | mm | | | inch | | |
|------|------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.20 | | 2.40 | 0.087 | | 0.094 |
| A1 | 0.90 | | 1.10 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.90 | 0.025 | | 0.035 |
| B2 | 5.20 | | 5.40 | 0.204 | | 0.213 |
| C | 0.45 | | 0.60 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.60 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| E | 6.40 | | 6.60 | 0.252 | | 0.260 |
| G | 4.40 | | 4.60 | 0.173 | | 0.181 |
| H | 9.35 | | 10.10 | 0.368 | | 0.398 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.60 | | 1.00 | 0.024 | | 0.039 |
| V2 | 0° | | 8° | 0° | | 0° |



DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

REEL MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|-------|--------|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0.795 | |
| G | 16.4 | 18.4 | 0.645 | 0.724 |
| N | 50 | | 1.968 | |
| T | | 22.4 | | 0.881 |

| BASE QTY | BULK QTY |
|----------|----------|
| 2500 | 2500 |

TAPE MECHANICAL DATA

| DIM. | mm | | inch | |
|------|------|------|-------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 6.8 | 7 | 0.267 | 0.275 |
| B0 | 10.4 | 10.6 | 0.409 | 0.417 |
| B1 | | 12.1 | | 0.476 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.5 | | 0.059 | |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 7.4 | 7.6 | 0.291 | 0.299 |
| K0 | 2.55 | 2.75 | 0.100 | 0.108 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 7.9 | 8.1 | 0.311 | 0.319 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 40 | | 1.574 | |
| W | 15.7 | 16.3 | 0.618 | 0.641 |

* on sales type

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